General Purpose Transistor

NPN Silicon

BC846BM3T5G, NSVBC846BM3T5G

Features

• Moisture Sensitivity Level: 1

• ESD Rating: Human Body Model: >4000 V

Machine Model: >400 V

 NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

• This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	65	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C	P _D	265	mW
Derate above 25°C		2.1	mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate (Note 2) TA = 25°C	P _D	640	mW
Derate above 25°C		5.1	mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	195	°C/W
Junction and Storage Temperature Range	T_J , T_{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

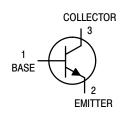
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 1



1B = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BC846BM3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSVBC846BM3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC846BM3T5G, NSVBC846BM3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•				
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	65	_	-	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A, V_{EB} = 0$)	V _{(BR)CES}	80	-	-	V
Collector – Base Breakdown Voltage (I _C = 10 μA)	V _{(BR)CBO}	80	-	-	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	6.0	-	-	V
Collector Cutoff Current $(V_{CB} = 30 \text{ V})$ $(V_{CB} = 30 \text{ V}, T_{A} = 150^{\circ}\text{C})$	I _{CBO}	- -	- -	15 5.0	nA μA
Base Peak Current $(t \le 1 s)$	I _{BM}	_	-	200	mA
ON CHARACTERISTICS	•				
DC Current Gain $ (I_C = 10 \ \mu\text{A}, \ V_{CE} = 5.0 \ \text{V}) $ $ (I_C = 2.0 \ \text{mA}, \ V_{CE} = 5.0 \ \text{V}) $	h _{FE}	_ 200	150 290	- 450	_
Collector – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{CE(sat)}	-	- -	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}	-	0.7 0.9	- -	V
Base – Emitter Voltage (I_C = 1.0 mA, V_{CE} = 5.0 V) (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	V _{BE(on)}	550 580 -	645 660 –	700 700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	_	-	4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	_	-	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846BM3T5G, NSVBC846BM3T5G

TYPICAL CHARACTERISTICS

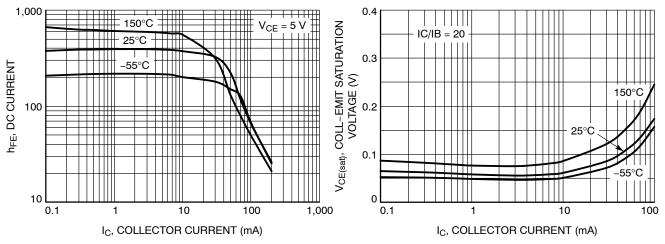


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

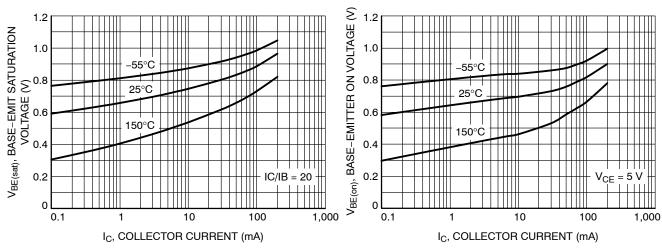


Figure 3. Base-Emitter Saturation Voltage

V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) 2.0 = 25°C Î HIIII I_C = 200 mA 10 mA 20 mA 50 mA 100 mA 1.6 1.2 8.0 0.4 1,000 0.01 0.1 10 100 IB, BASE CURRENT (mA)

Figure 4. Base-Emitter "On" Voltage

IC, COLLECTOR CURRENT (mA) Figure 5. Base-Emitter Temperature

10

-55°C to 150°C

100

Figure 6. Collector Saturation Region

θ_{VB}, TEMPERATURE COEFFICIENT (mV)

-0.2

-0.6

-1.0

-1.4

-1.8

-2.2

-2.6

0.1

= 5 V

 $\theta_{\mbox{\scriptsize VB}},$ for $\mbox{\scriptsize V}_{\mbox{\scriptsize BE}}$

BC846BM3T5G, NSVBC846BM3T5G

TYPICAL CHARACTERISTICS

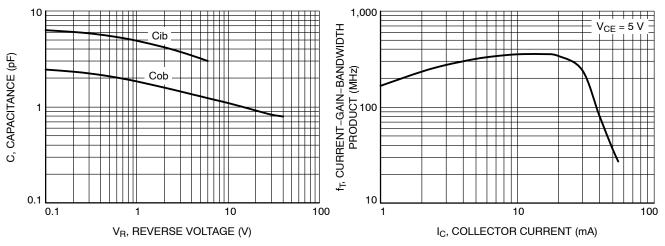


Figure 7. Capacitances

Figure 8. Current-Gain-Bandwidth Product



SOT-723 CASE 631AA-01 ISSUE D

DATE 10 AUG 2009

NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.45	0.50	0.55	
b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
E	0.75	0.80	0.85	
е	0.40 BSC			
ΗE	1.15	1.20	1.25	
L	0.29 REF			
L2	0.15	0.20	0.25	

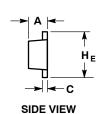
GENERIC MARKING DIAGRAM*

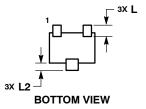


= Specific Device Code XX Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

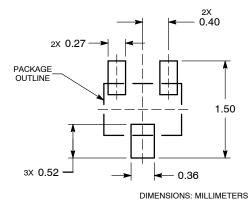
-X-2X b ⊕ 0.08 X Y **TOP VIEW**





STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SOT-723		PAGE 1 OF 1	

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